



**DMN100** 

#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features**

- Extremely Low On-Resistance:  $170m\Omega$  @  $V_{GS} = 4.5V$
- High Drain Current: 1.1A
- Ideal for Notebook Computer, Portable Phone, PCMCIA Cards, and Battery Powered Circuits
- **ESD Protected Gate**
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

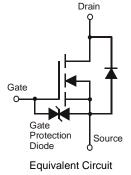
### **Mechanical Data**

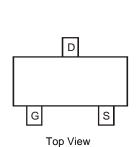
- Case: SC59
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.014 grams (approximate)





Top View





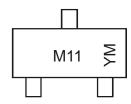
Ordering Information (Note 3)

Part Number	Case	Packaging
DMN100-7-F	SC59	3000/Tape & Reel

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.

- 2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

## **Marking Information**



M11 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006)M = Month (ex: 9 = September)

Date Code Key

Notes:

Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	Т	U	V	W	Χ	Υ	Z	Α	В	С	D	E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		$V_{DSS}$	30	V
Gate-Source Voltage	Continuous	$V_{GSS}$	±20	V
Drain Current	Continuous Pulsed	ID	1.1 4.0	А

### Thermal Characteristics @TA = 25°C unless otherwise specified

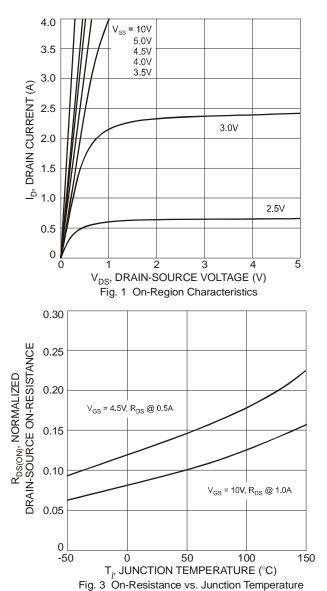
Characteristic	Symbol	Value	Units
Total Power Dissipation	$P_{D}$	500	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	250	K/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

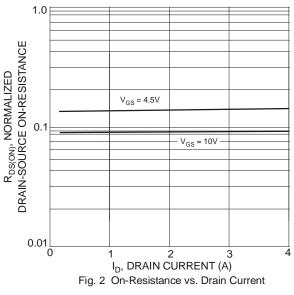
## Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

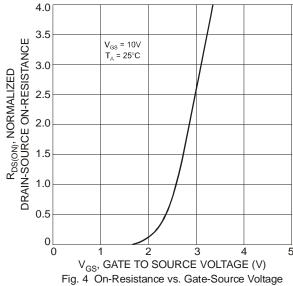
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 4)				ā.					
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	30		_	V	$V_{GS} = 0V, I_D = 250 \mu A$		
Zero Gate Voltage Drain Current	@ T <sub>J</sub> = 25°C @ T <sub>J</sub> = 125°C	I <sub>DSS</sub>	_	_	1.0 10	μА	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V		
Gate-Body Leakage		I <sub>GSS</sub>	_		± 100	nA	$V_{GS} = \pm 12V$ , $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 4)									
Gate Threshold Voltage		$V_{GS(th)}$	1.0	_	3.0	V	$V_{DS} = 10V, I_{D} = 1.0 \text{mA}$		
Static Drain-Source On-Resistance		R <sub>DS (ON)</sub>	_	_	0.170 0.150	Ω	$V_{GS} = 4.5V, I_D = 0.5A$ $V_{GS} = 10V, I_D = 1.0A$		
Forward Transconductance		g <sub>FS</sub>	1.3	2.4	_	S	$V_{DS} = 10V, I_{D} = 0.5A$		
DYNAMIC CHARACTERISTICS									
Input Capacitance		C <sub>iss</sub>	_	150	_	pF			
Output Capacitance		Coss	_	90		pF	$V_{DS} = 10V, V_{GS} = 0V$ - f = 1.0MHz		
Reverse Transfer Capacitance		Crss	_	30		pF	71 = 1.0101112		
Total Gate Charge		$Q_g$	_	5.5		nC	\/ 04\/ L 4.0A		
Gate-to-Source Charge		Qgs	_	8.0	_	nC	$V_{DS} = 24V, I_D = 1.0A,$		
Gate-to-Drain Charge		$Q_{gd}$	_	1.3		nC	V <sub>GS</sub> = 10V		
SWITCHING CHARACTERISTICS							•		
Turn-On Delay Time		t <sub>D(ON)</sub>	_	10	_	ns			
Turn-Off Delay Time		t <sub>D(OFF)</sub>	_	25	_	ns	$V_{DD} = 10V, I_D = 0.5A,$		
Turn-On Rise Time		tr	_	15		ns	$V_{GS} = 5.0V$ , $R_{GEN} = 50\Omega$		
Turn-Off Fall Time		t <sub>f</sub>	_	45		ns			
SOURCE-DRAIN RATINGS (BODY DIODE)									
Continuous Source Current		Is	_		0.54	Α	_		
Pulse Source Current		$I_{SM}$	_		4.0	Α	_		
Forward Voltage		V <sub>SD</sub>		_	1.2	V	$I_F = 1.0A, V_{GS} = 0V$		
Reverse Recovery Time	·	t <sub>rr</sub>		35	_	ns	$I_F = 1.0A$ , $di/dt = 50A/\mu s$		

Notes: 4. Pulse width  $\leq 300 \mu s, \ duty \ cycle \leq 2\%.$ 

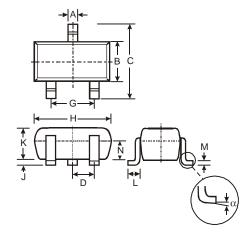








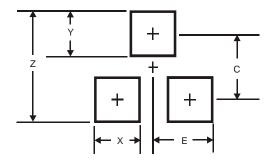
# **Package Outline Dimensions**



SC59							
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
C	2.70	3.00	2.80				
D	-	-	0.95				
G	-	-	1.90				
Н	2.90	3.10	3.00				
7	0.013	0.10	0.05				
K	1.00	1.30	1.10				
L	0.35	0.55	0.40				
М	0.10	0.20	0.15				
N	0.70	0.80	0.75				
α	0°	8°	-				
All Dimensions in mm							



### Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
Х	0.8
Υ	1.0
С	2.4
E	1.35

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>>Diodes Incorporated(达迩科技(美台))